

THE SPECIFICATION OF AlGaAs IR LED CHIP "IR4R-12"

1. DESCRIPTION

This is a AlGaAs red LED chip. It is N-side up. The peak wavelength is 810nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25deg. C)

CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage (Vf) IF=50mA		1.70	1.85	V
Reverse Voltage (Vr) IR=10uA	5			V
Radiated Power ¹⁾ (Po) IF=20mA	2.5	3.5		mW
Peak Wavelength (λp) IF=20mA		810		nm
Spectral Radiation Bandwidth (Δλ) IF=20mA		35		nm

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

Reverse Voltage : 5 V(IR=10uA)
 Storage Temperature : 0 to 40 deg. C
 while on mylar membrane : 0 to 40 deg. C
 after removal from mylar membrane : -30 to 100 deg. C

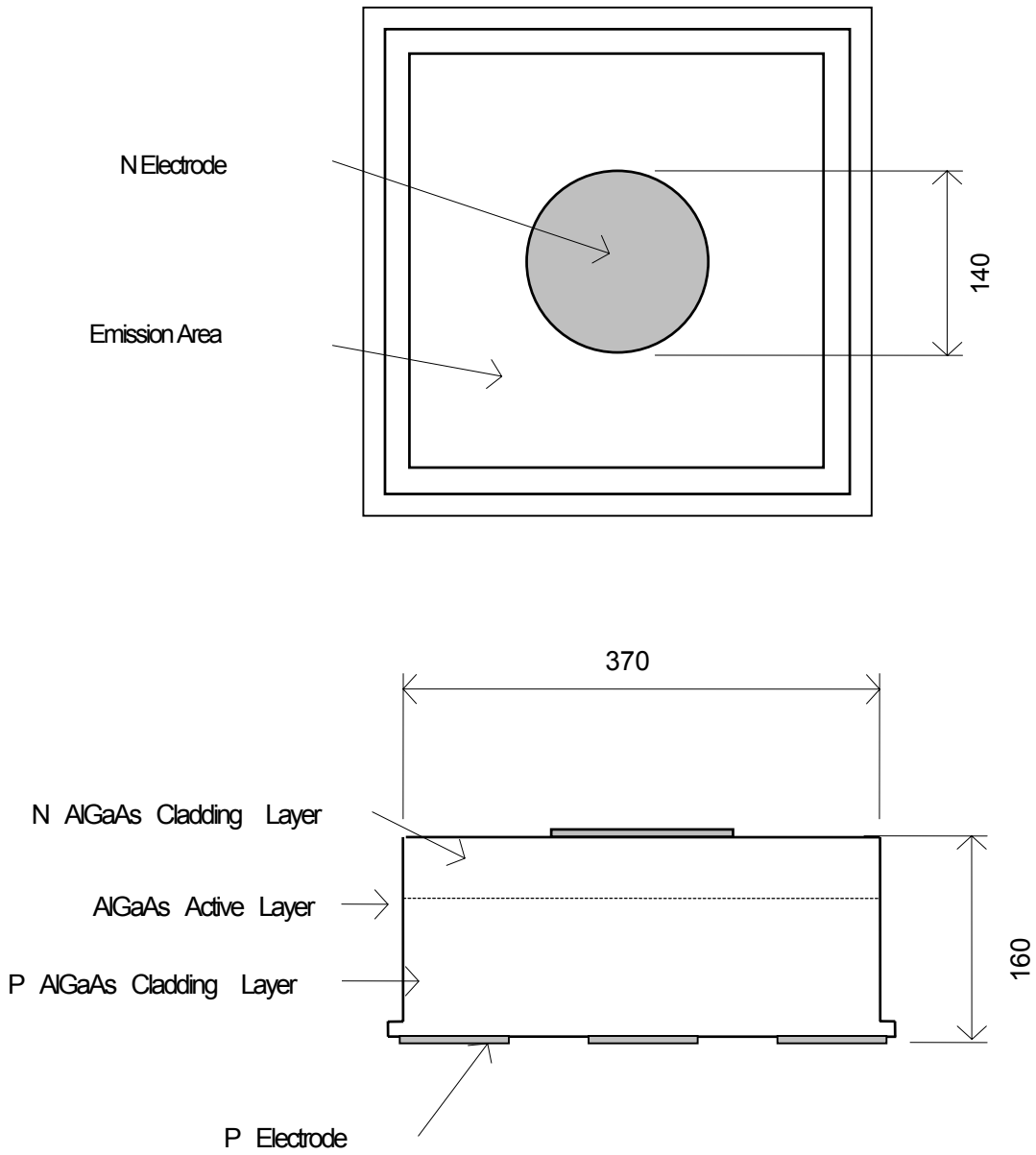
4. PHYSICAL CHARACTERISTICS AND STRUCTURE

1)Material : AlGaAs
 2)Structure : Double Hetero Structure
 3)Junction Size : 0.370mmX0.370mm
 4)Thickness : 0.160mm
 5)Bond Pad Size : 0.140mm diameter
 6)Anode Metallization : Gold Alloy
 7)Cathode Metallization : Gold Alloy

Physical Dimensions

Model IR4R

Unit: um



Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.